

## REMARKS

This application has been reviewed in light of the Office Action dated July 14, 2004. Claims 25-29, 33-39, and 59 are pending in this application. Claim 59 has been added to provide Applicants with a more complete scope of protection. Claim 25 is in independent form. Favorable reconsideration is requested.

The specification has been amended to cross-reference the above-identified application to parent application No. 10/083,585 (now U.S. Patent No. 6,720,237). Applicants submit that the objection to the specification has been obviated and therefore Applicants respectfully request withdrawal of this objection.

The Office Action rejected Claims 25-29 and 34-39 under 35 U.S.C. § 103(a) as being unpatentable over U.S. Patent No. 5,856,229 (Sakaguchi) and U.S. Patent No. 6,274,937 (Ahn) in view of U.S. Patent No. 6,548,382 (Henley) and U.S. Patent No. 6,486,008 (Lee); and rejected Claim 33 under 35 U.S.C. § 103(a) as being unpatentable over Sakaguchi and Ahn in view of Henley and Lee, and further in view of U.S. Patent No. 6,222,167 (Wada). Applicants respectfully traverse these rejections.

Applicants submit that independent Claim 25, together with the remaining claims dependent thereon, are patentably distinct from the proposed combination of the cited prior art at least for the following reasons.

The aspect of the present invention set forth in Claim 25 is a method for manufacturing a semiconductor film. The method includes the step of preparing a first member including a semiconductor substrate, a semiconductor layer whose resistivity is higher than a resistivity of the semiconductor substrate, and a separation layer provided between the semiconductor substrate and the semiconductor layer. The method also

includes the step of separating the semiconductor layer from the semiconductor substrate at the separation layer by heating the first member by induction heating.

Among other important features of Claim 25 is utilizing a difference of resistivity between a semiconductor substrate and a semiconductor layer and separating the semiconductor layer from the semiconductor substrate at the separation layer by heating the first member by induction heating.

Ahn et al., as understood by Applicants, relates to a silicon multi-chip module packaging with integrated passive components and a method of making the packaging. The Office Action states that Ahn et al. teaches that "... resistivity of GaAs is inherently higher than that of the Si" (col. 3, lines 1-3). Applicants submit that the resistivity of GaAs greatly changes in accordance with dope amount of impurities just as that of Si does, and the relation of the resistivity between GaAs and Si is not determined unequivocally. In addition, Ahn et al., at col. 3, lines 1-3, states that "[s]ilicon substrates suffer from lower substrate resistivity when compared to GaAs." Applicants submit that even if this statement is true, nothing in this section, or any other section of Ahn et al. would teach or suggest a method for manufacturing a semiconductor film that includes a step of preparing a first member including a semiconductor substrate, where the semiconductor layer has a resistivity is higher than a resistivity of the semiconductor substrate.

Accordingly, Applicants submit that at least for this reason, Claim 25 is patentable over the cited prior art, when taken separately or in any proposed combination (assuming that such combination is even permissible).

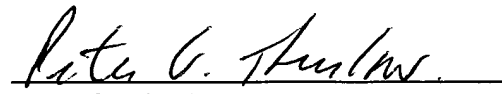
A review of the other art of record, including Wada, has failed to reveal anything that, in Applicants' opinion, would remedy the deficiencies of the art discussed above, as applied against the independent claims herein. Therefore, those claims are respectfully submitted to be patentable over the art of record.

The other rejected claims in this application depend from independent Claim 25 as discussed above, and, therefore, are submitted to be patentable for at least the same reasons. Since each dependent claim is also deemed to define an additional aspect of the invention, individual consideration or reconsideration, as the case may be, of the patentability of each claim on its own merits is respectfully requested.

In view of the foregoing amendments and remarks, Applicants respectfully request favorable reconsideration and the allowance of the present application.

Applicants' undersigned attorney may be reached in our New York Office by telephone at (212) 218-2100. All correspondence should continue to be directed to our address listed below.

Respectfully submitted,

A handwritten signature in cursive script, reading "Peter G. Thurlow", is written over a horizontal line.

Peter G. Thurlow  
Attorney for Applicants  
Registration No.: 47,138

FITZPATRICK, CELLA, HARPER & SCINTO  
30 Rockefeller Plaza  
New York, New York 10112-3801  
Facsimile: (212) 218-2200